



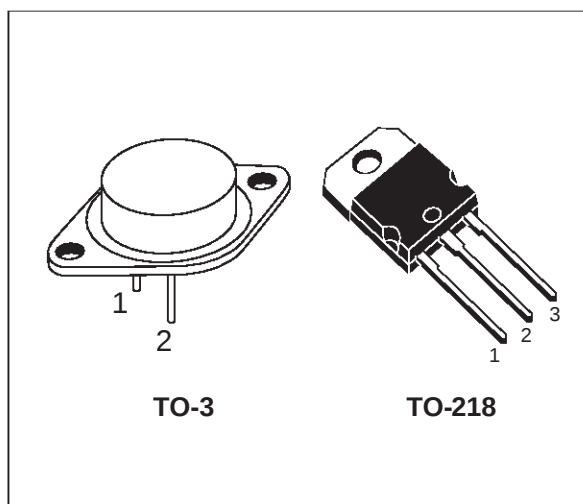
BU931
BU931P

HIGH VOLTAGE IGNITION COIL DRIVER NPN POWER DARLINGTON

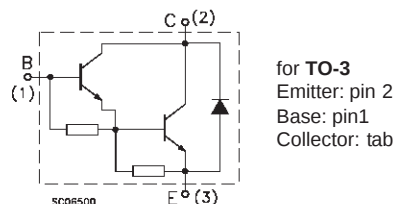
- VERY RUGGED BIPOLAR TECHNOLOGY
- HIGH OPERATING JUNCTION TEMPERATURE
- WIDE RANGE OF PACKAGES

APPLICATIONS

- HIGH RUGGEDNESS ELECTRONIC IGNITIONS



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		BU931	BU931P	
V_{CES}	Collector-Emitter Voltage ($V_{BE} = 0$)	500		V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	400		V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	5		V
I_C	Collector Current	15		A
I_{CM}	Collector Peak Current	30		A
I_B	Base Current	1		A
I_{BM}	Base Peak Current	5		A
P_{tot}	Total Dissipation at $T_C = 25\text{ }^{\circ}\text{C}$	175	135	W
T_{stg}	Storage Temperature	-65 to 200	-65 to 175	$^{\circ}\text{C}$
T_j	Max. Operating Junction Temperature	200	175	$^{\circ}\text{C}$

THERMAL DATA

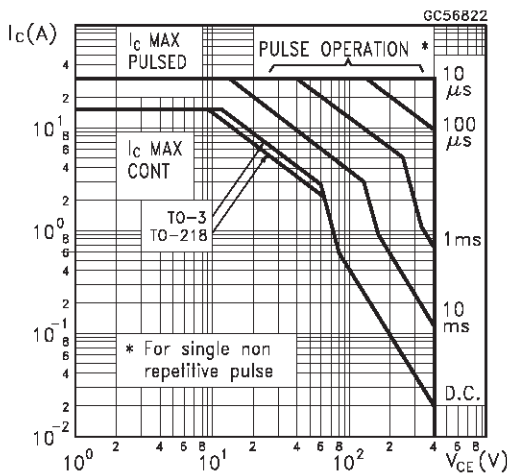
		TO-3	TO-218	
$R_{thj-case}$	Thermal Resistance Junction-case Max	1	1.1	$^{\circ}\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}\text{C}$ unless otherwise specified)

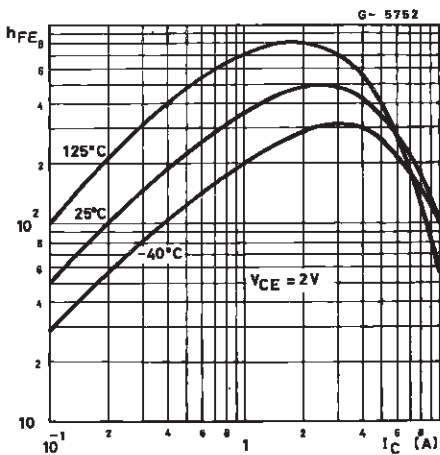
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CES}	Collector Cut-off Current ($V_{BE} = 0$)	$V_{CE} = 500\text{ V}$ $V_{CE} = 500\text{ V}$ $T_j = 125^{\circ}\text{C}$			100 0.5	μA mA
I_{CEO}	Collector Cut-off Current ($I_B = 0$)	$V_{CE} = 450\text{ V}$ $V_{CE} = 450\text{ V}$ $T_j = 125^{\circ}\text{C}$			100 0.5	μA mA
I_{EBO}	Emitter Cut-off Current ($I_C = 0$)	$V_{EB} = 5\text{ V}$			20	mA
$V_{CEO(sus)}^*$	Collector-Emitter Sustaining Voltage ($I_B = 0$)	$I_C = 100\text{ mA}$ $L = 10\text{ mH}$ $V_{Clamp} = 400\text{ V}$ (See Fig.4)	400			V
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage	$I_C = 7\text{ A}$ $I_B = 70\text{ mA}$ $I_C = 8\text{ A}$ $I_B = 100\text{ mA}$ $I_C = 10\text{ A}$ $I_B = 250\text{ mA}$			1.6 1.8 1.8	V V V
$V_{BE(sat)}^*$	Base-Emitter Saturation Voltage	$I_C = 7\text{ A}$ $I_B = 70\text{ mA}$ $I_C = 8\text{ A}$ $I_B = 100\text{ mA}$ $I_C = 10\text{ A}$ $I_B = 250\text{ mA}$			2.2 2.4 2.5	V V V
h_{FE}^*	DC Current Gain	$I_C = 5\text{ A}$ $V_{CE} = 10\text{ V}$	300			
V_F	Diode Forward Voltage	$I_F = 10\text{ A}$			2.5	V
	Functional Test (see fig. 1)	$V_{CC} = 24\text{ V}$ $V_{clamp} = 400\text{ V}$ $L = 7\text{ mH}$	8			A
t_s t_f	INDUCTIVE LOAD Storage Time Fall Time (see fig. 3)	$V_{CC} = 12\text{ V}$ $V_{clamp} = 300\text{ V}$ $L = 7\text{ mH}$ $I_C = 7\text{ A}$ $I_B = 70\text{ mA}$ $V_{BE} = 0$ $R_{BE} = 47\ \Omega$		15 0.5		μs μs

* Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

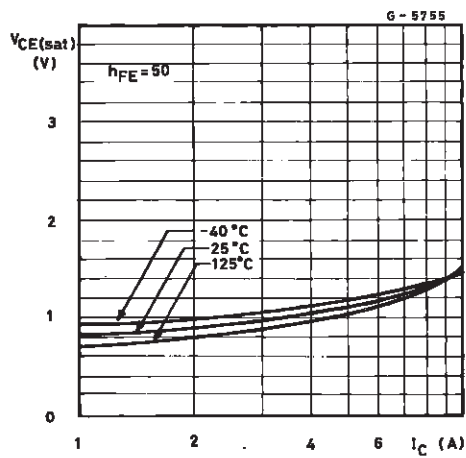
Safe Operating Area



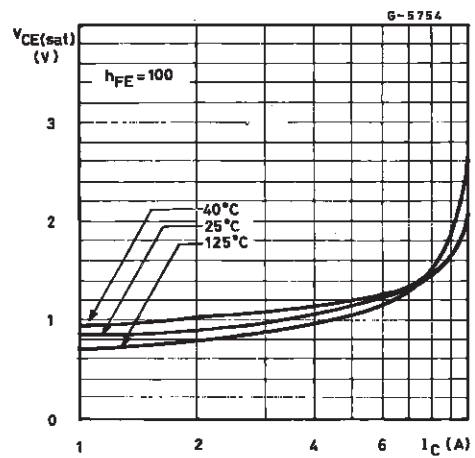
DC Current Gain



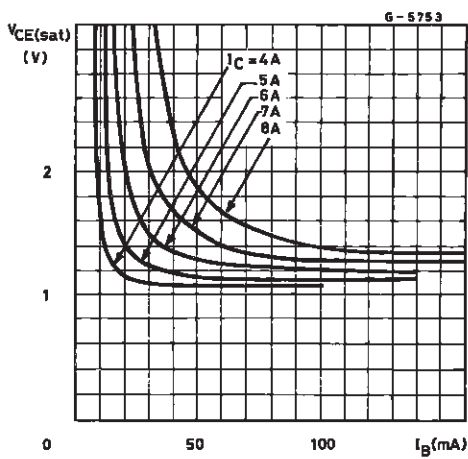
Collector Emitter Saturation Voltage



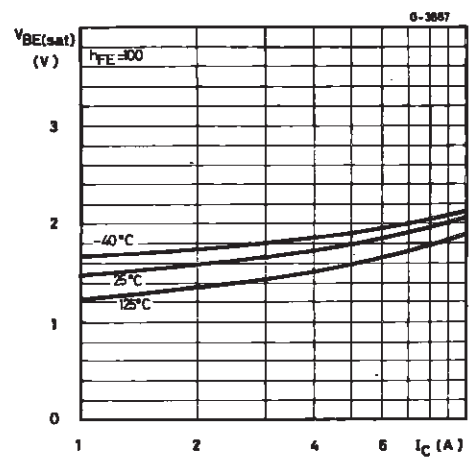
Collector Emitter Saturation Voltage



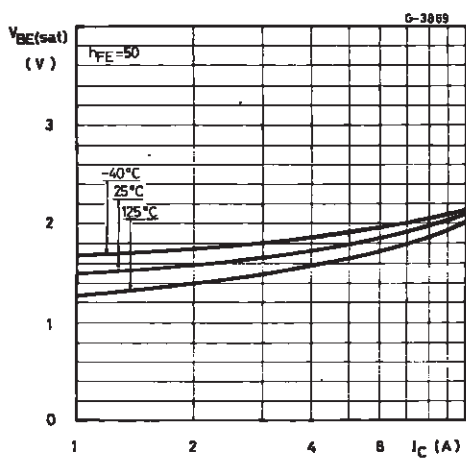
Collector Emitter Saturation Voltage



Base Emitter Saturation Voltage



Base Emitter Saturation Voltage



Switching Time Inductive Load

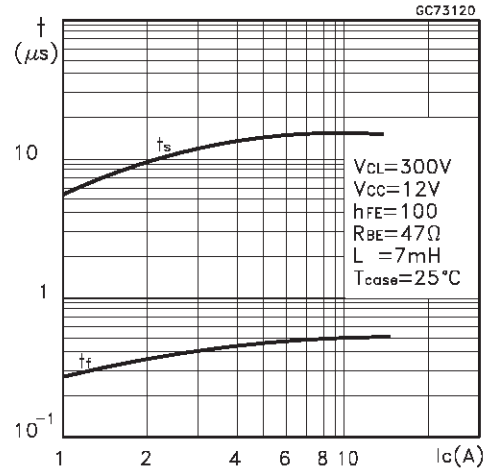


FIGURE 1: Functional Test Circuit

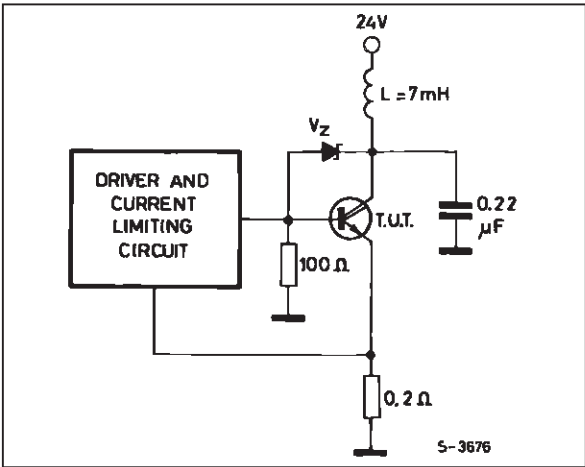


FIGURE 2: Functional Test Waveforms

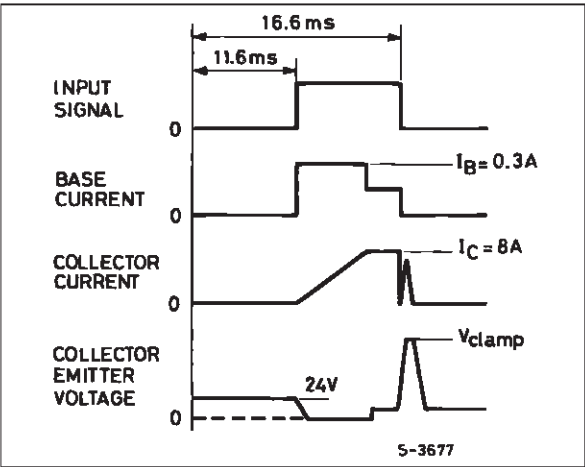


FIGURE 3: Switching Time Test Circuit

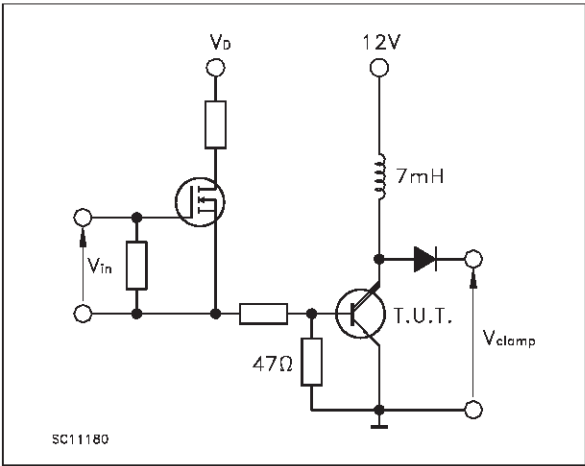
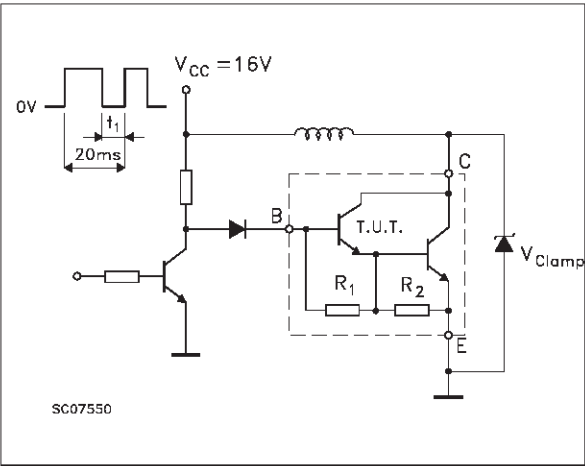
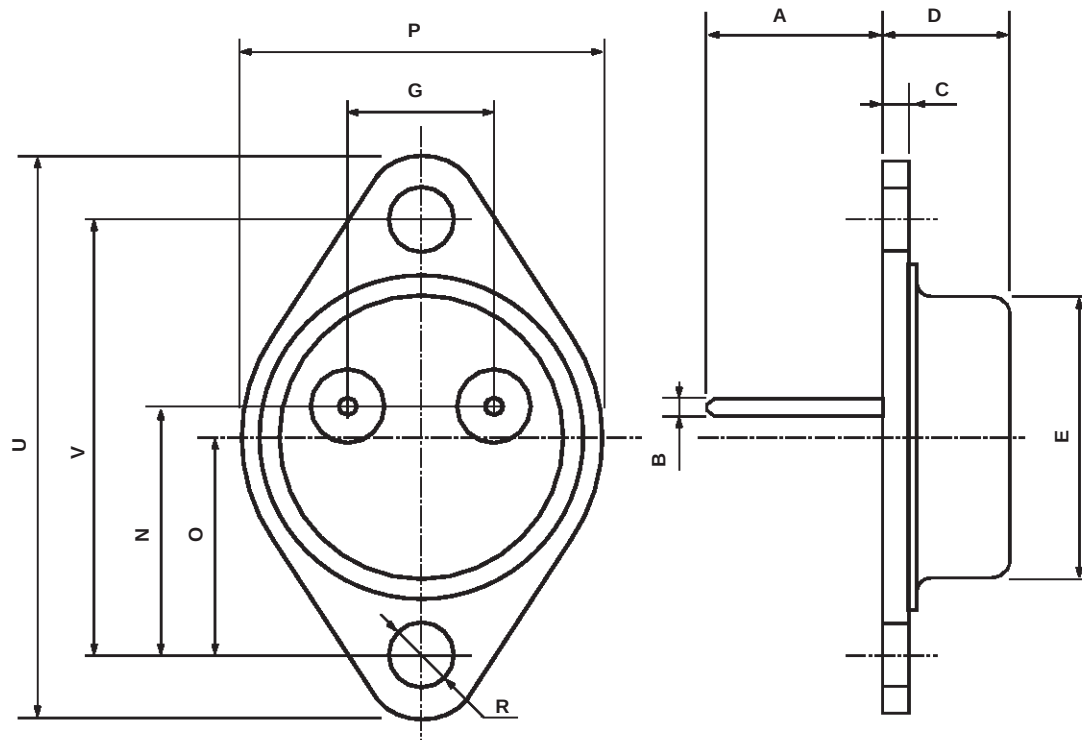


FIGURE 4: Sustaining Voltage Test Circuit



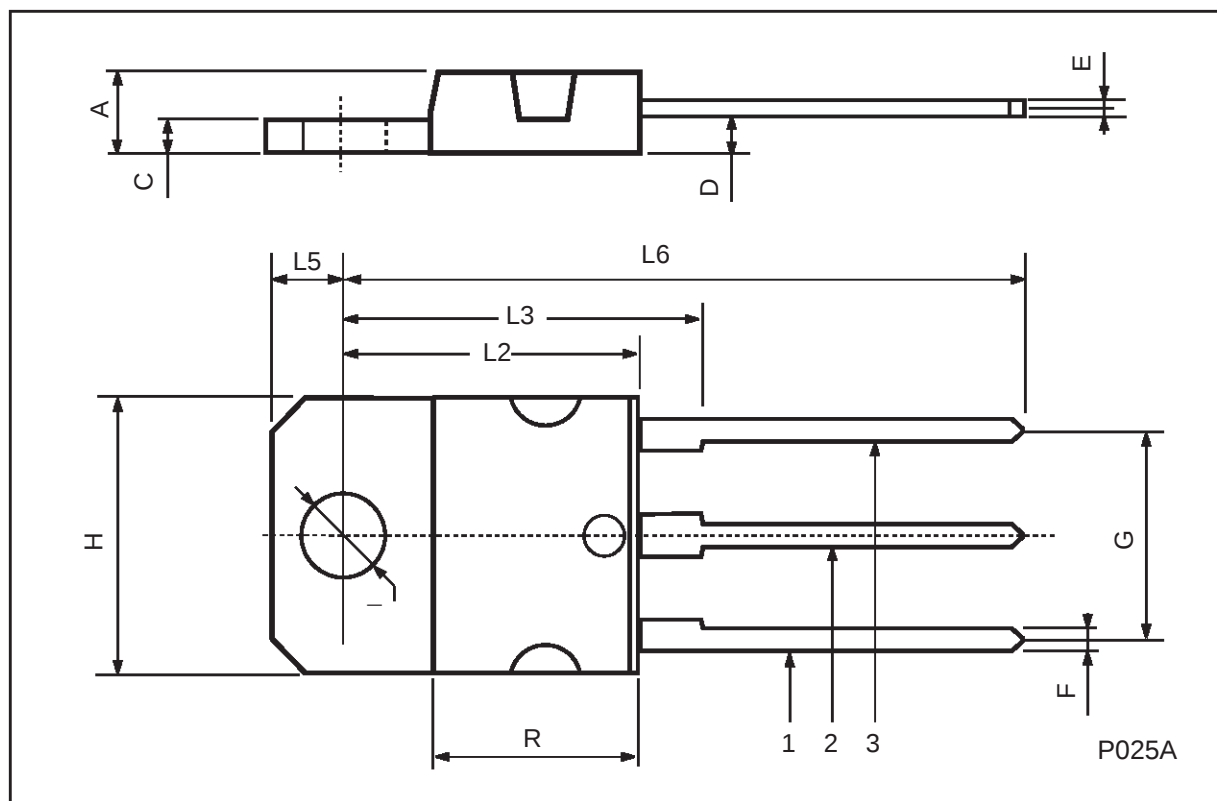
TO-3 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	11.00		13.10	0.433		0.516
B	0.97		1.15	0.038		0.045
C	1.50		1.65	0.059		0.065
D	8.32		8.92	0.327		0.351
E	19.00		20.00	0.748		0.787
G	10.70		11.10	0.421		0.437
N	16.50		17.20	0.649		0.677
P	25.00		26.00	0.984		1.023
R	4.00		4.09	0.157		0.161
U	38.50		39.30	1.515		1.547
V	30.00		30.30	1.187		1.193



P003F

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.7		4.9	0.185		0.193
C	1.17		1.37	0.046		0.054
D		2.5			0.098	
E	0.5		0.78	0.019		0.030
F	1.1		1.3	0.043		0.051
G	10.8		11.1	0.425		0.437
H	14.7		15.2	0.578		0.598
L2	–		16.2	–		0.637
L3		18			0.708	
L5	3.95		4.15	0.155		0.163
L6		31			1.220	
R	–		12.2	–		0.480
Ø	4		4.1	0.157		0.161



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